

SANYO

No.829H

2SA1481/2SC2960

PNP/NPN Epitaxial Planar Silicon Transistors

High-Speed Switching Applications

Features

- . Fast switching speed
- . High breakdown voltage

(): 2SA1481

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)150	mA
Collector Current(Pulse)	I_{CP}	(-)400	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

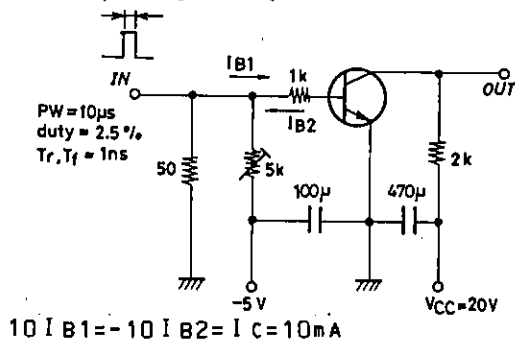
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)6V, I_C=(-)1mA$	100*		560*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)1mA$		100		MHz
Output Capacitance	c_{ob}	$V_{CB}=(-)6V, f=1MHz$		2.7(4.0)		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10mA, I_B=(-)1mA$	(-)0.1		(-)0.4	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)10mA, I_B=(-)1mA$	(-)0.75		(-)1.1	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)5			V
Delay Time	t_d	See specified Test Circuit.		40	60	ns
Rise Time	t_r	"		80(120)130(230)		ns
Storage Time	t_{stg}	"		230(190)450(700)		ns
Fall Time	t_f	"		160(240)250(390)		ns

*: The 2SA1481/2SC2960 are classified by 1mA h_{FE} as follows:

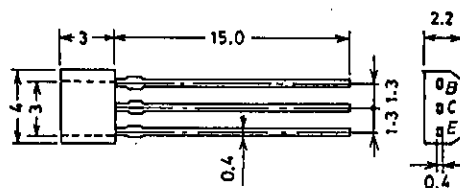
100	E	200	160	F	320	280	G	560
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Switching Time Test Circuit

(For PNP, the polarity is reversed.)

Unit(Resistance: Ω , Capacitance: F)**Package Dimensions 2033**

(unit: mm)

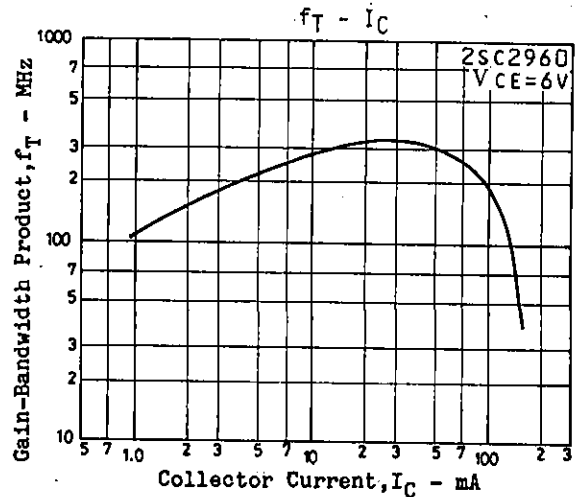
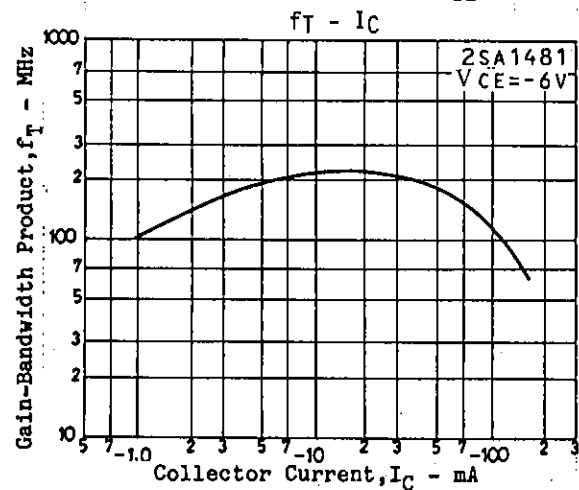
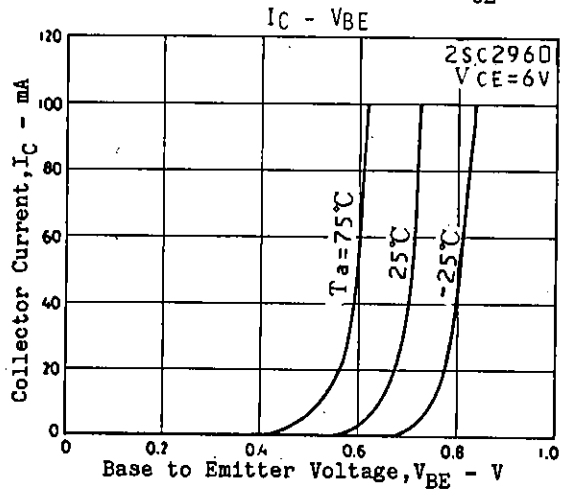
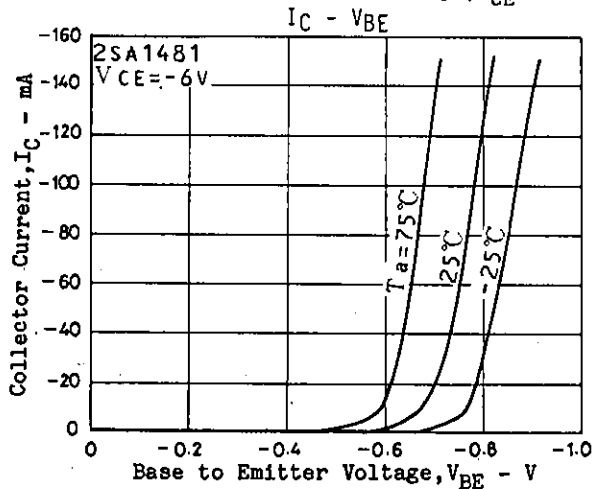
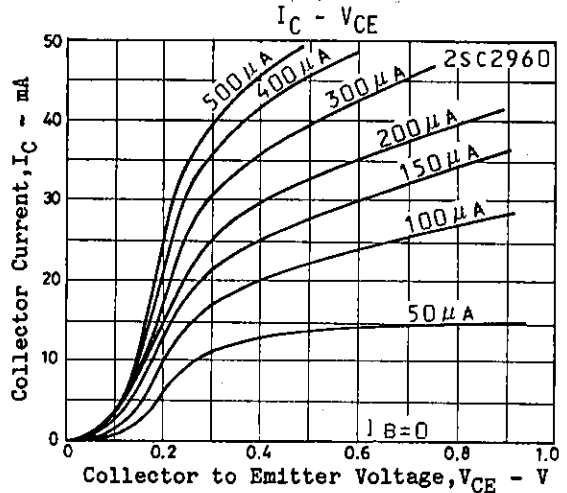
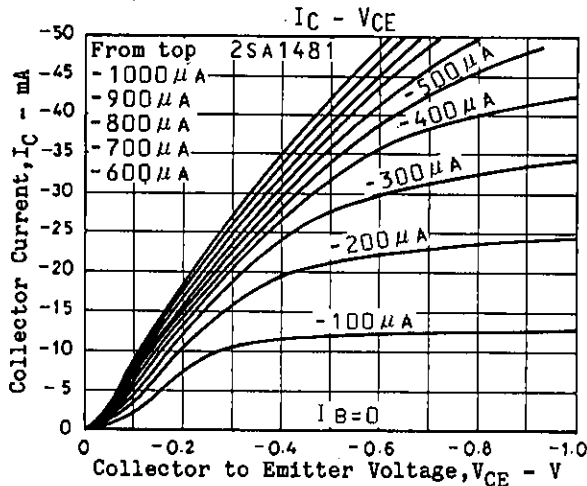
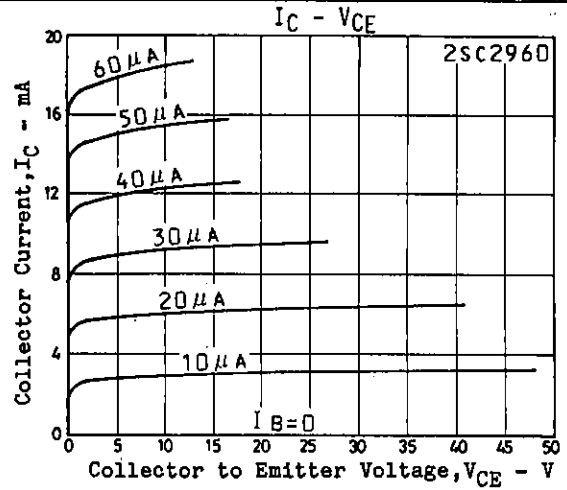
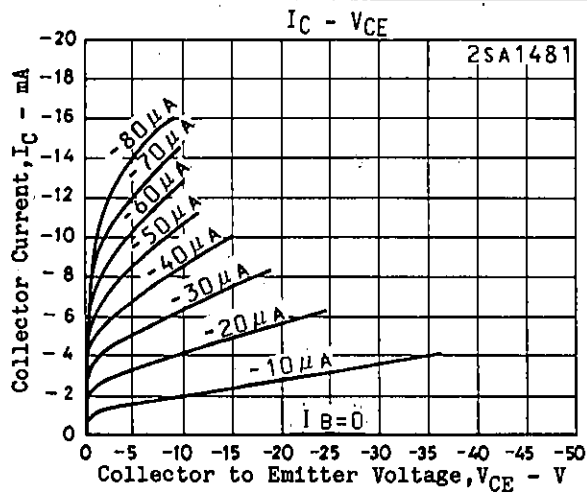


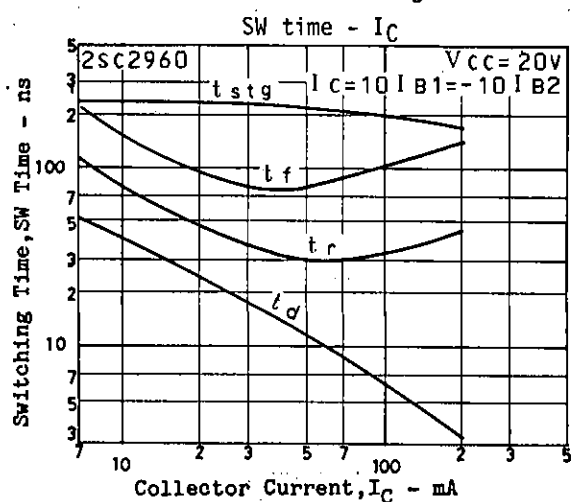
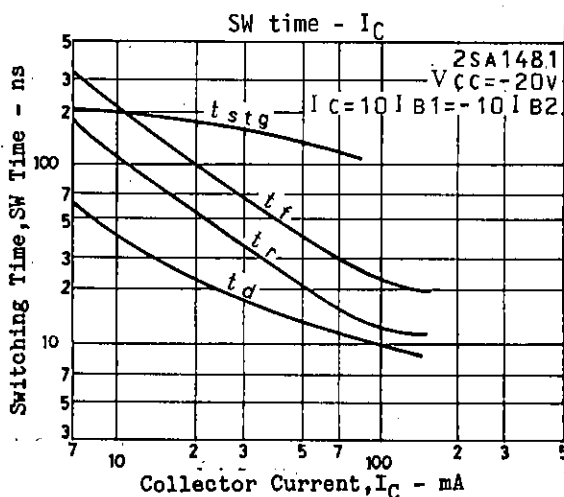
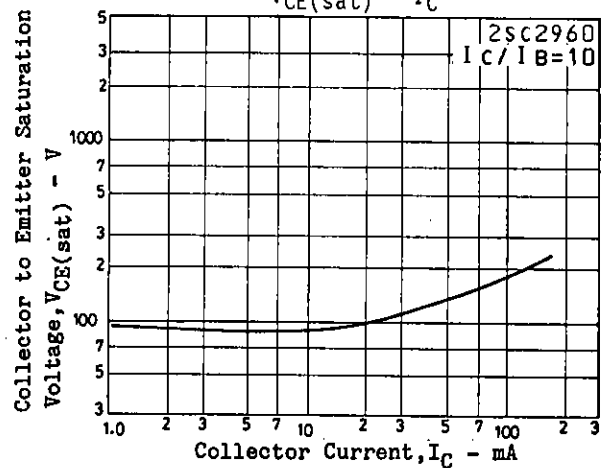
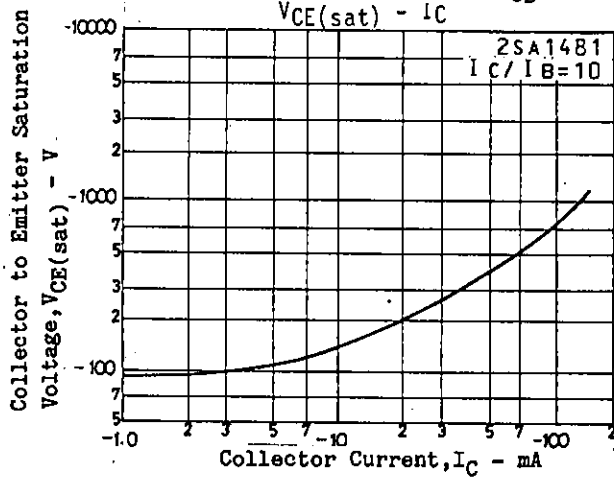
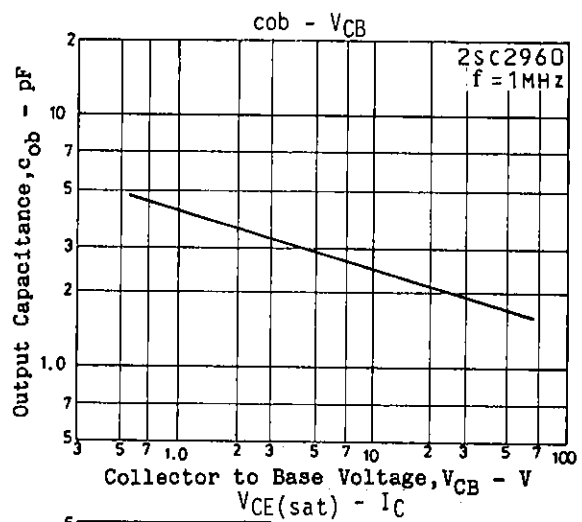
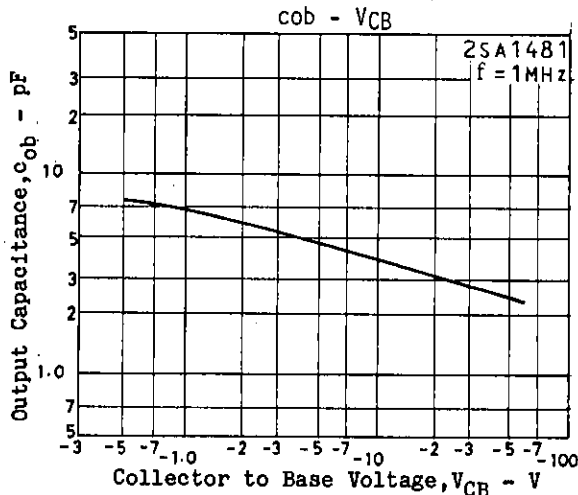
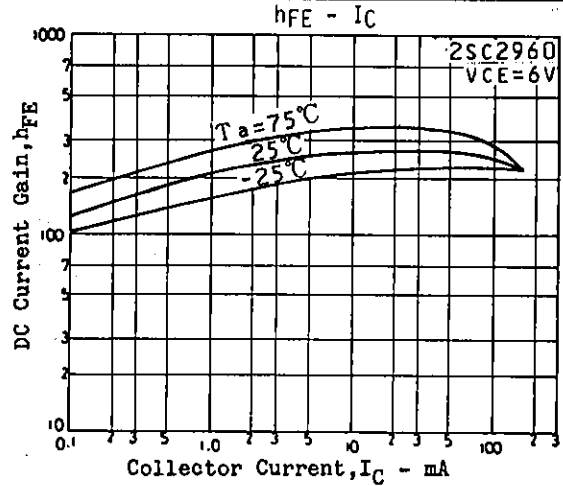
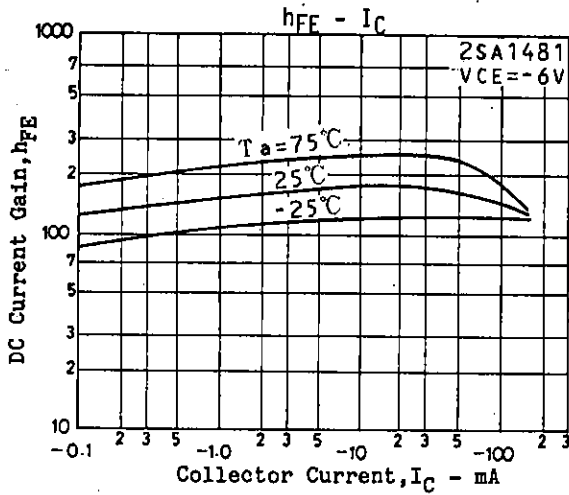
B: Base
C: Collector
E: Emitter

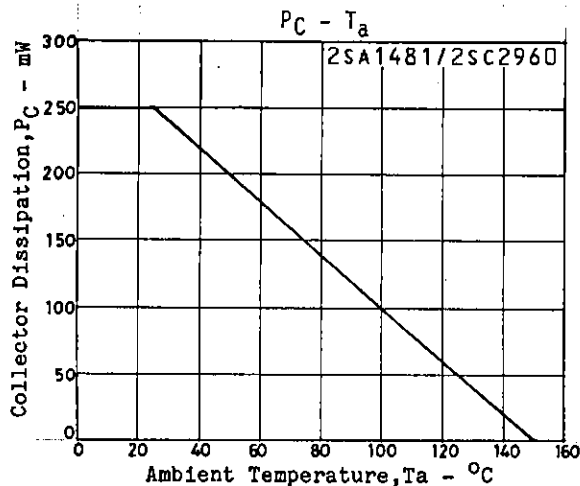
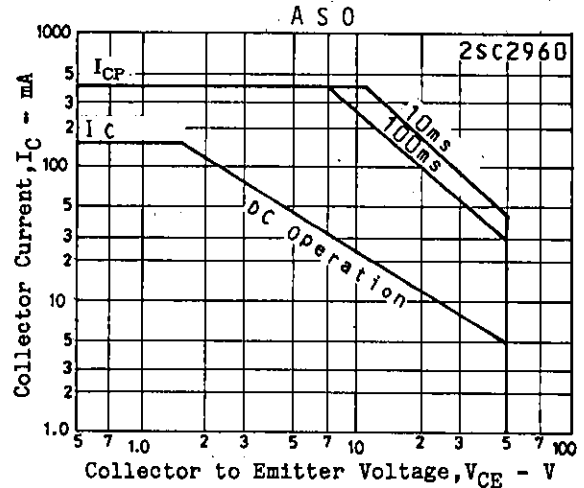
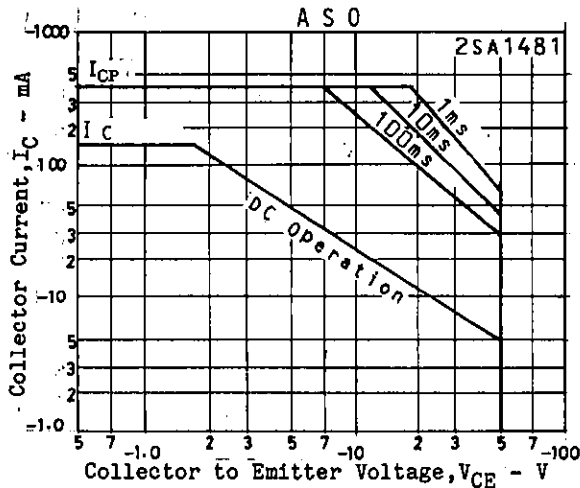
SANYO: SPA

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN







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